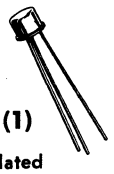
2N1008, A, B (GERMANIUM)
2N1008B JAN AVAILABLE



CASE 31(1)
(TO-5)
All leads isolated

PNP germanium transistor for audio driver and medium speed switching applications.

MAXIMUM RATINGS

Rating	Symbol	2N1008	2N1008A	2N1008B	Unit
Collector-Base Voltage	V_{CB}	20	40	60	Vdc
Collector-Emitter Voltage	V_{CEO}	20	40	60	Vdc
Emitter-Base Voltage	V_{EB}		15		Vdc
Collector Current	I_C		300		mAdc
Base Current	I_B		30		mAdc
Collector Dissipation T_A = 25°C derate T_C = 25°C derate	P_D		200 2.78 300 4.0		 mW mW/°C mW mW/°C
Junction and Storage Temperature Range	T_J, T_{stg}		-65 to +100		°C

ELECTRICAL CHARACTERISTICS (T_A = 25°C unless otherwise noted)

Characteristics	Symbol	Min	Typ	Max	UNIT
Collector Leakage Current	I_{CBO}				μAdc
(V_{CB} = 10 Vdc) 2N1008		---	5.0	10	
(V_{CB} = 10 Vdc, T_A = 85°C) 2N1008		---	---	500	
(V_{CB} = 25 Vdc) 2N1008A		---	5.0	10	
(V_{CB} = 25 Vdc, T_A = 85°C) 2N1008A		---	---	500	
(V_{CB} = 45 Vdc) 2N1008B		---	7.0	15	
(V_{CB} = 45 Vdc, T_A = 85°C) 2N1008B		---	---	750	
Emitter Leakage Current	I_{EBO}				μAdc
(V_{EB} = 10 Vdc) 2N1008		---	5.0	10	
2N1008A		---	---	10	
2N1008B		---	---	10	
Collector-Emitter Breakdown Voltage	BV_{CER}				Vdc
(I_C = 1.0 mAdc, R_{BE} = 10 K)					
2N1008		15	---	---	
2N1008A		35	---	---	
2N1008B		55	---	---	
Collector-Emitter Saturation Voltage (I_C = 100 mAdc, I_B = 10 mAdc)	V_{CE} (sat)	---	---	0.25	Vdc
Small Signal Current Gain (I_C = -10 mAdc, V_{CE} = 5.0 Vdc, f = 1 kHz)	h_{fe}	40	---	150	---
Input Resistance (V_{CB} = 6 V, I_E = 1 mA)	h_{ie}	200	---	1000	ohms